



**40V P-CHANNEL ENHANCEMENT MODE MOSFET** 

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-40V	80mΩ @ V <sub>GS</sub> = -10V	-3.7 A
	150mΩ @ V <sub>GS</sub> = -4.5V	-2.8 A

#### Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

#### Applications

- Motor Control
- DC-DC Converters
- **Power Management Functions**
- Uninterrupted Power Supply

#### **Features and Benefits**

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

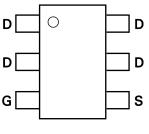
#### **Mechanical Data**

- Case: SOT26
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.018 grams (Approximate)

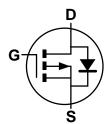




Top View



Top View Pin-Out



**Equivalent Circuit** 

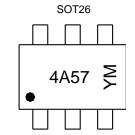
#### Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Quantity per reel
ZXMP4A57E6TA	Standard	SOT26	3,000
ZXMP4A57E6QTA	Automotive	SOT26	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product\_grade\_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**



4A57 = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: C = 2015) M or  $\overline{M}$  = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022
Code	C	D	F	F	G	H	1	.1
Jour	0		_					U

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	-40	V
Gate-Source Voltage			V <sub>GS</sub>	±20	V
		(Note 7)		-3.7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 7)}$	$I_{D}$	-2.9	Α
		(Note 6)		-2.9	
Pulsed Drain Current	V <sub>GS</sub> = 10V	(Note 8)	I <sub>DM</sub>	-18	Α
Continuous Source Current (Body Diode) (Note 7)		Is	-2.6	Α	
Pulsed Source Current (Body Diode) (Note 8)		I <sub>SM</sub>	-18	А	

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)		1.1	
Linear Derating Factor	(Note 7)	P <sub>D</sub>	1.7 13.7	mW/°C
Thormal Basistanas, Junatian to Ambient	(Note 6)	D	113	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R <sub>θJA</sub>	73	C/VV
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

Notes:

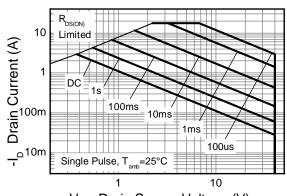
<sup>6.</sup> For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

<sup>7.</sup> Same as Note 4, except the device is measured at  $t \le 5$  seconds.

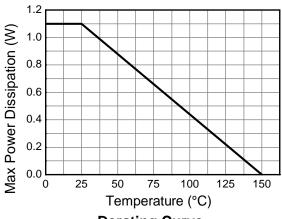
<sup>8.</sup> Same as Note 4, except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.



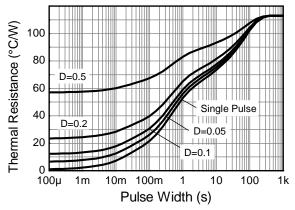
## Thermal Characteristics



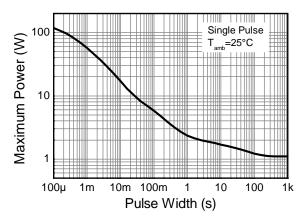
-V<sub>DS</sub> Drain-Source Voltage (V) **P-channel Safe Operating Area** 



**Derating Curve** 



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 



#### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

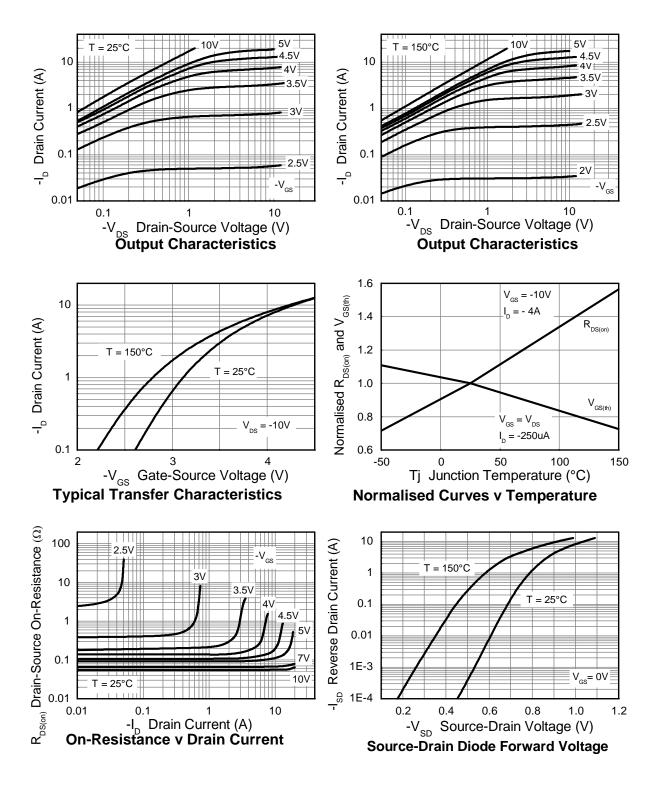
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-40	_	_	V	$I_D = -250 \mu A, V_{GS}$	s = 0V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-0.5	μΑ	$V_{DS} = -40V, V_{GS}$	= 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS}$	= 0V
ON CHARACTERISTICS						•	
Gate Threshold Voltage	$V_{GS(th)}$	-1.0		-3.0	٧	$I_D = -250 \mu A, V_{DS}$	= V <sub>GS</sub>
Static Drain-Source On-Resistance (Note 9)	D			0.080	Ω	$V_{GS} = -10V, I_D =$	-4A
Static Dialii-Source Off-Resistance (Note 9)	R <sub>DS(ON)</sub>			0.150	12	$V_{GS} = -4.5V, I_{D} =$	: -2A
Forward Transconductance (Notes 9 & 10)	g <sub>fs</sub>		7.6	_	S	$V_{DS} = -15V, I_{D} =$	-4A
Diode Forward Voltage (Note 9)	$V_{SD}$	_	-0.86	-0.95	V	$I_S = -4A$ , $V_{GS} = 0V$	
Reverse Recovery Time (Note 10)	t <sub>rr</sub>	_	17.4	_	ns		
Reverse Recovery Charge (Note 10)	Q <sub>rr</sub>	_	11.1	_	nC	$I_S = -1.8A$ , di/dt =	= 100A/μS
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C <sub>iss</sub>		833	_		.,	2) /
Output Capacitance	Coss		122	_	pF	$V_{DS} = -20V, V_{GS}$ f = 1MHz	= 0V
Reverse Transfer Capacitance	C <sub>rss</sub>		78	_		1 - 1111112	
Total Gate Charge (Note 11)	Qg	_	7	_		$V_{GS} = -4.5V$	
Total Gate Charge (Note 11)	Qg	_	15.8	_	200		$V_{DS} = -20V$
Gate-Source Charge (Note 11)	Qgs	_	3.6	_	$\begin{array}{c c} - & nC \\ V_{GS} = -10V \\ \end{array}$		$I_D = -4A$
Gate-Drain Charge (Note 11)	$Q_{gd}$	_	2.7	_			
Turn-On Delay Time (Note 11)	t <sub>D(on)</sub>	_	2.5	_		V <sub>DD</sub> = -20V, V <sub>GS</sub> = -10V	
Turn-On Rise Time (Note 11)	t <sub>r</sub>		3.3	—			
Turn-Off Delay Time (Note 11)	t <sub>D(off)</sub>	_	47	_	ns	$I_D = -1A$ , $R_G \cong 6$ .	Ω0
Turn-Off Fall Time (Note 11)	t <sub>f</sub>		21				

Notes:

- 9. Measured under pulsed conditions. Pulse width  $\leq$  300µs; duty cycle  $\leq$  2%. 10. For design aid only, not subject to production testing. 11. Switching characteristics are independent of operating junction temperatures.

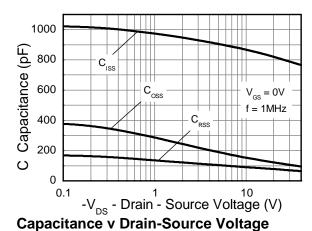


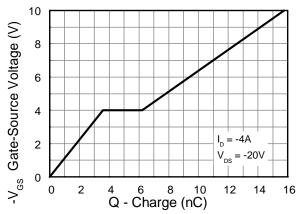
#### **Typical Characteristics**





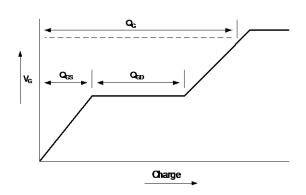
#### Typical Characteristics (cont.)





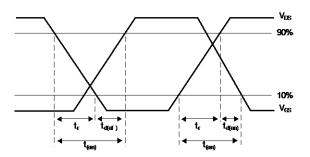
**Gate-Source Voltage v Gate Charge** 

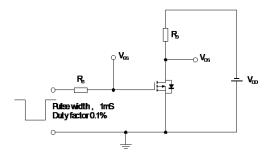
## **Test Circuits**



Basic gate charge waveform

Gate charge test circuit





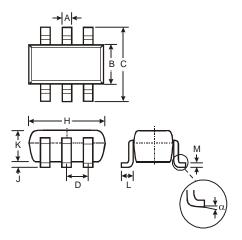
Switching time waveforms

Switching time test circuit



#### **Package Outline Dimensions**

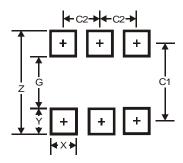
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SOT26							
Dim	Min	Max	Тур					
Α	0.35	0.50	0.38					
В	1.50	1.70	1.60					
С	2.70	3.00	2.80					
D	_	_	0.95					
Н	2.90	3.10	3.00					
J	0.013	0.10	0.05					
K	1.00	1.30	1.10					
L	0.35	0.55	0.40					
М	0.10	0.20	0.15					
α	0°	8°	_					
All D	imensi	ons in	mm					

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.95



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TK31J60W5,S1VQ(O 2SK2614(TE16L1,Q) DMN1017UCP3-7 EFC2J004NUZTDG FCAB21350L1 P85W28HP2F-7071 DMN1053UCP4-7

NTE2384 NTE2969 NTE6400A DMN2080UCB4-7 DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 SSM6P54TU,LF DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7 STF5N65M6 STU5N65M6 C3M0021120D DMN13M9UCA6-7

BSS340NWH6327XTSA1 MCM3400A-TP DMTH10H4M6SPS-13 IRF40SC240ARMA1 IPS60R1K0PFD7SAKMA1

IPS60R360PFD7SAKMA1 IPS60R600PFD7SAKMA1